

REMARKS/ARGUMENTS

Claims 12, 23, 35-36, 40-44, 46-51, and 58-59 have been amended to correct minor errors and to place the application in better condition for allowance. No new matter has been added.

Attached hereto is a marked-up version of the changes made to the claims by the current amendment. The attached page is captioned "Version with markings to show changes made."

In view of the above, each of the presently pending claims in this application is believed to be in immediate condition for allowance. Accordingly, the Examiner is respectfully requested to pass this application to issue.

Dated: November 26, 2002

Respectfully submitted,

By 

Thomas J. D'Amico

Registration No.: 28,371

Mialeeka C. Williams-Bibbs

Registration No.: 48,037

DICKSTEIN SHAPIRO MORIN &

OSHINSKY LLP

2101 L Street NW

Washington, DC 20037-1526

(202) 785-9700

Attorneys for Applicants

Version With Markings to Show Changes Made

12. (Amended) The method of claim 11 wherein said step of processing comprises heating said silver-germanium-selenide glass to a temperature at or slightly below a thin-film glass transition temperature of said silver-germanium-selenide glass.

23. (Amended) The method of claim 21 wherein said step of annealing comprises the step of heating said metal containing resistance variable material to a temperature at or slightly below a thin-film glass transition temperature of said metal containing resistance variable material.

35. (Amended) The [device] element of claim 34 wherein said glass has a germanium molar concentration number greater than about 0.23.

36. (Amended) The [device] element of claim 34 wherein said glass has a mean coordination number of at least about 2.46.

40. (Amended) The [device] element of claim 39 wherein said metal is silver.

41. (Amended) The [device] element of claim 39 wherein said annealed metal containing resistance variable material comprises a germanium-selenide glass.

42. (Amended) The [device] element of claim 41 wherein said germanium-selenide glass has a germanium molar concentration number of greater than about 0.23.

43. (Amended) The [device] element of claim 39 wherein said annealed metal containing resistance variable material has a mean coordination number of at least about 2.46.

44. (Amended) The [device] element of claim 39 wherein said annealed metal containing resistance variable material comprises a silver doped germanium-selenide.

46. (Amended) The [device] element of claim 45 wherein said metal comprises silver.

47. (Amended) The [device] element of claim 45 wherein said annealed metal containing resistance variable material comprises a germanium-selenide glass.

48. (Amended) The [device] element of claim 47 wherein said germanium-selenide glass has a germanium molar concentration number of greater than about 0.23.

49. (Amended) The [device] element of claim 45 wherein said annealed metal containing resistance variable material has a mean coordination number of at least about 2.46.

50. (Amended) The [device] element of claim 45 wherein said annealed metal containing resistance variable material comprises a silver doped germanium-selenide.

51. (Amended) A computer device having a memory, said memory comprising:

an annealed metal containing resistance variable material having increased rigidity.

58. (Amended) The [device] element of claim 57 wherein said annealed resistance variable material comprises silver.

59. (Amended) The [device] element of claim 57 wherein said annealed resistance variable material comprises a germanium-selenide glass.